PDFN3×3A-8L N MOS

N-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

V_{DS} (V) = 60V

I_D =24 A (V_{GS} = ±20V)

$R_{DS(ON)}$@10V≤13mR(Typ.11.5mR)

AEC-Q101 。Qualified to AEC-Q101 Standards for High Reliability, HF Product.

DC/DC

These devices are well suited for high efficiehs q q q q :

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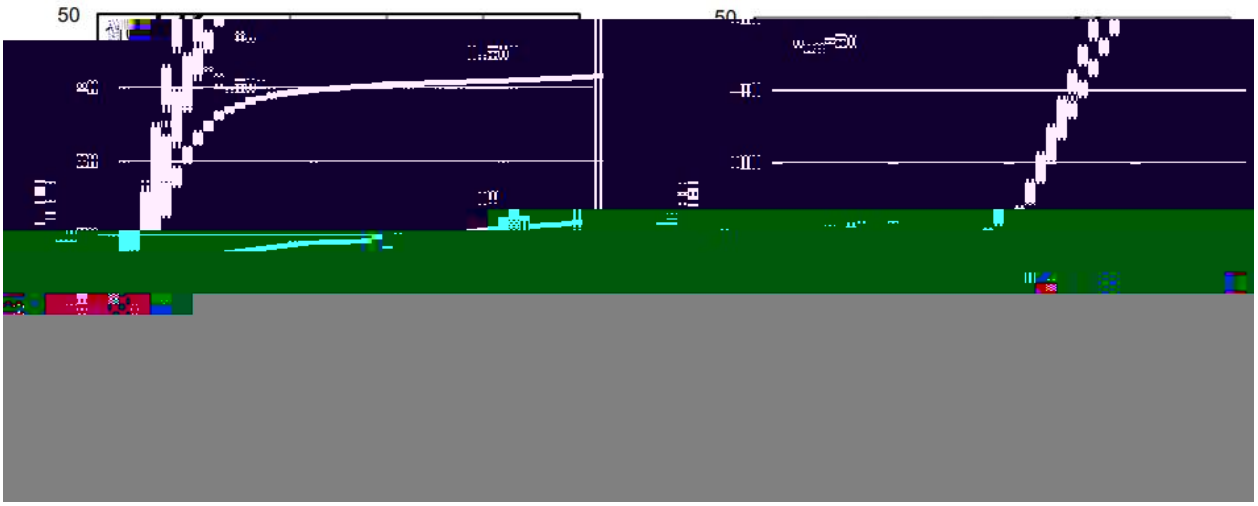
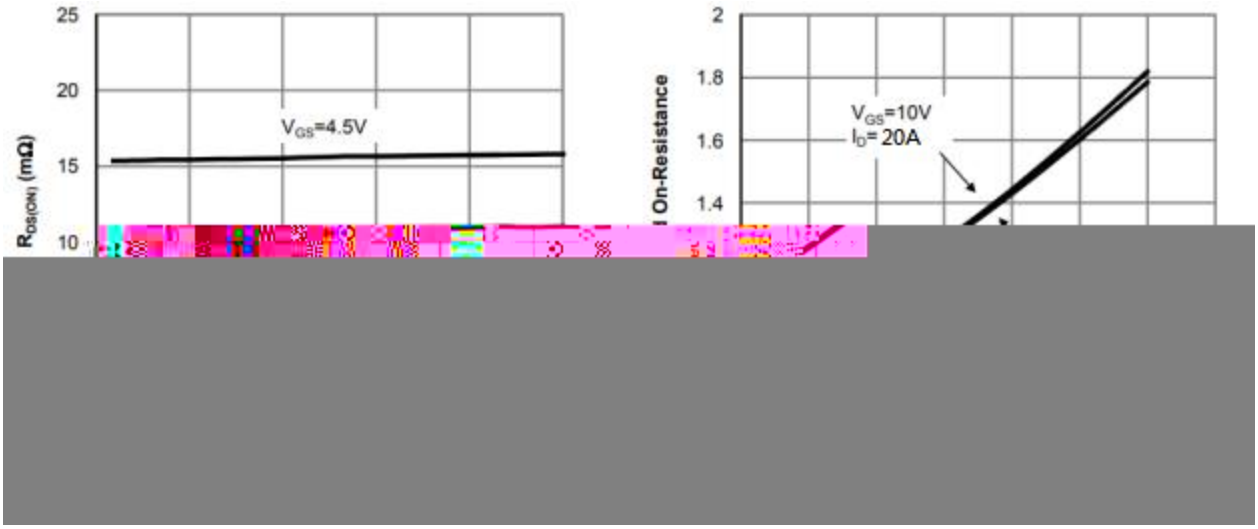
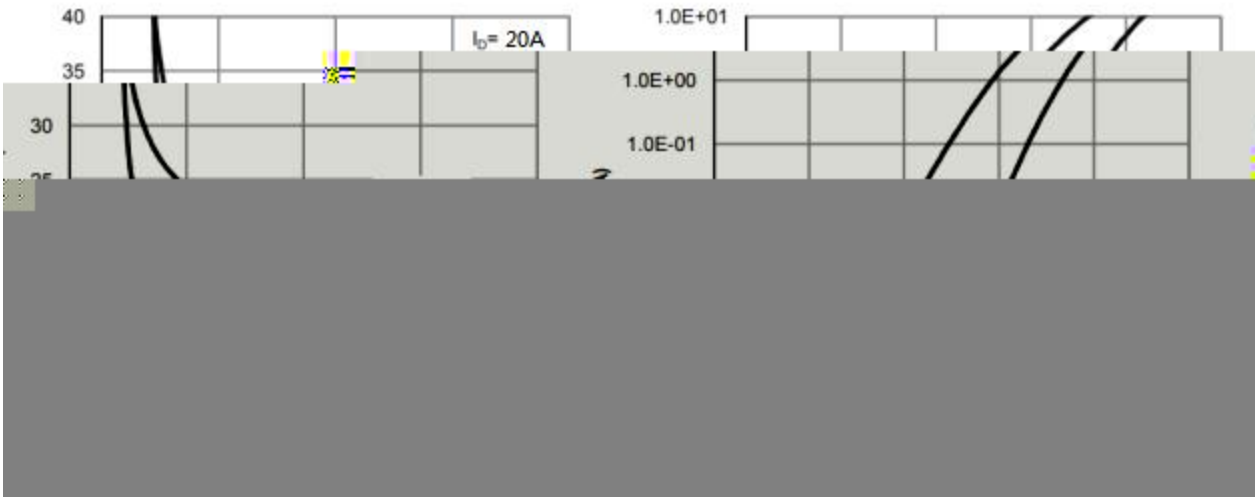
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V	I_D=250μA	60	64		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V	V_{GS}=0V			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			±0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250μA	1.0	1.6	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V	I_D=20A		11.5	13	mΩ
		V_{GS}=4.5V	I_D=10A		15.5	18	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V	I_S=1A			1.2	V
Input Capacitance	C_{iss}	V_{DS}=25V f=1.0MHz	V_{GS}=0V		1010		pF
Output Capacitance	C_{oss}				250		
Reverse Transfer Capacitance	C_{rss}				280		
Gate resistance	R_g	V_{GS}=0V f=1MHz	V_{DS}=0V		1.5		Ω
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V I_D=13A	V_{DS}=30V		13.5		nC
Total Gate Charge	$Q_{g(4.5V)}$				6.5		
Gate Source Charge	Q_{gs}				2.5		
Gate Drain Charge	Q_{gd}				3.0		
Turn-On DeR		O					

/ Electrical Characteristic Curve







/ Marking Instructions

BR Q
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Note:

BR:	Company Code
Q:	Automobile halogen-free product Code
120N06:	Product Type Code
****:	Lot No. Code, code change with Lot No

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